



**1N483B thru
1N486B and
1N5194 thru
1N5196**

SANTA ANA, CA
For more information call:
(714) 979-8220

FEATURES

- Voidless hermetically sealed glass package (D0-35).
- Triple layer passivation.
- Metallurgically bonded.
- TX types available per MIL-S-19500/118C.
- 1N5194 thru 1N5196 only available in surface mount.

MAXIMUM RATINGS

Operating Temperature: -65°C to +200°C.
Storage Temperature: -65°C to +200°C.
Surge Current: 2A

ELECTRICAL CHARACTERISTICS

TYPE	WORKING PEAK REVERSE VOLTAGE V _{RWM}	BREAKDOWN VOLTAGE (MIN.) V _(BR) @ 100 µA	AVERAGE RECTIFIED CURRENT I _O		FORWARD VOLTAGE DROP (MAX.) V _F	REVERSE CURRENT (MAX.) I _R @ V _{RWM}		SURGE CURRENT (MAX.) (NOTE 1) I _S SURGE	JUNCTION CAPACITANCE C _J @ 0V	
			AMPS			VOLTS	µA			
			25°C	150°C			25°C			150°C
JAN 1N483B	70	80	.2	.05	1.0V (pk) @ 100mA pulse	.025	5	2	8	
JAN 1N485B	180	200	.2	.05		.025	5	2	8	
JAN 1N486B	225	250	.2	.05		.025	5	2	8	
JAN 1N5194 JAN 1N5195 JAN 1N5196	SAME AS JAN 1N483B SAME AS JAN 1N485B SAME AS JAN 1N486B				} EXCEPT: PACKAGE D035					

PACKAGE: D07 for JAN 1N483B, 485B, 486B.
D035 for JAN 1N5194, JAN 1N5195, and JAN 1N5196.

NOTE 1: I_O = 200mAdc, 10 - 8.3msec surges

MECHANICAL CHARACTERISTICS

Case: Hermetically sealed glass case.
Lead Material: Tinned copper.
Marking: Body painted, alpha numeric.
Polarity: Cathode band.

**GENERAL PURPOSE
SILICON DIODES**

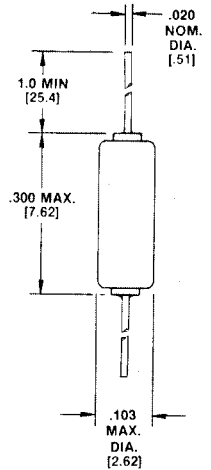


FIGURE 1A
PACKAGE D07

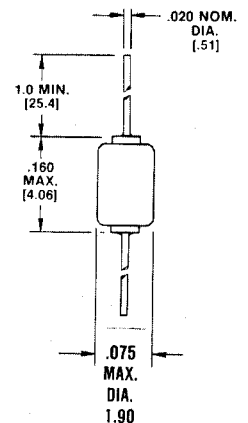


FIGURE 1B
PACKAGE D0-35

1N483B - 1N486B. 1N5194 - 1N5196

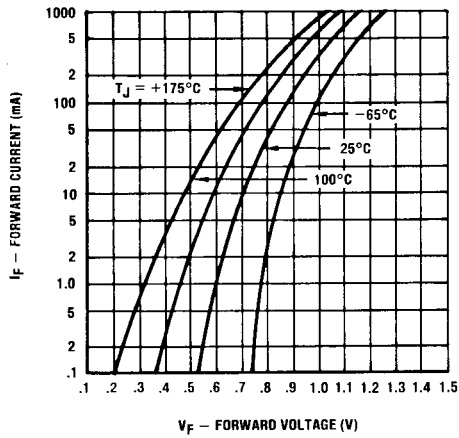


FIGURE 2
FORWARD VOLTAGE vs. FORWARD CURRENT

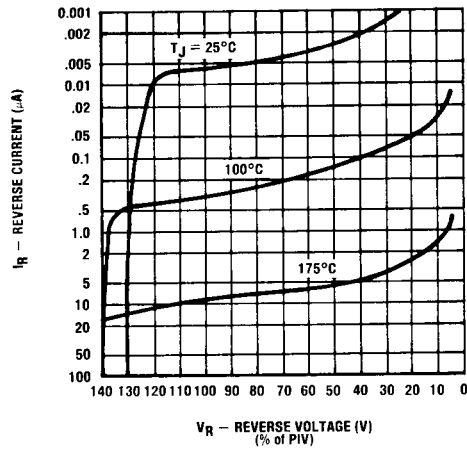


FIGURE 3
REVERSE VOLTAGE vs. REVERSE CURRENT